

Vishay Siliconix

Dual N-Channel 20-V (D-S) MOSFET

| PRODUCT SUMMARY | | | | | | |
|---------------------|----------------------------------|---------------------------------|-----------------------|--|--|--|
| V _{DS} (V) | R _{DS(on)} (Ω) | I _D (A) ^a | Q _g (Typ.) | | | |
| 20 | 0.046 at V_{GS} = 4.5 V | 4.5 | 3.5 nC | | | |
| | 0.063 at V _{GS} = 2.5 V | 4.5 | 3.5 110 | | | |

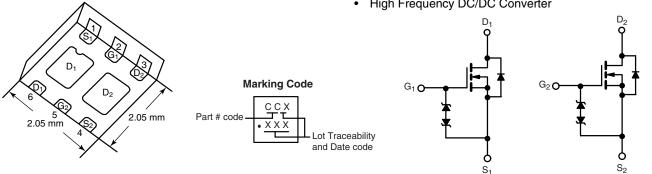
PowerPAK SC-70-6 Dual

FEATURES

- Halogen-free According to IEC 61249-2-21
- TrenchFET[®] Power MOSFET New Thermally Enhanced PowerPAK®
- SC-70 Package - Small Footprint Area
 - Low On-Resistance
- Typical ESD Protection 560 V

APPLICATIONS

- Load Switch for Portable Applications
- High Frequency DC/DC Converter



Ordering Information: SiA906EDJ-T1-GE3 (Lead (Pb)-free and Halogen-free)

N-Channel MOSFET

N-Channel MOSFET

| ABSOLUTE MAXIMUM RATIN | IGS T _A = 25 °C, | unless othe | erwise noted | | |
|--|------------------------------------|-----------------------------------|------------------------|------|--|
| Parameter | | Symbol | Limit | Unit | |
| Drain-Source Voltage | | V _{DS} | 20 | V | |
| Gate-Source Voltage | | V _{GS} | ± 12 | | |
| | T _C = 25 °C | - I _D - | 4.5 ^a | | |
| Continuous Drain Current (T _J = 150 °C) | T _C = 70 °C | | 4.5 ^a | | |
| | T _A = 25 °C | | 4.5 ^{a, b, c} | | |
| | T _A = 70 °C | | 4.1 ^{b, c} | А | |
| Pulsed Drain Current | | I _{DM} | 15 | | |
| Continuous Source-Drain Diode Current | T _C = 25 °C | | 4.5 ^a | | |
| | T _A = 25 °C | ا _S | 1.6 ^{b, c} | | |
| Maximum Power Dissipation | T _C = 25 °C | | 7.8 | | |
| | T _C = 70 °C | P _D | 5 | w | |
| | T _A = 25 °C | | 1.9 ^{b, c} | •• | |
| | T _A = 70 °C | | 1.2 ^{b, c} | | |
| Operating Junction and Storage Temperature Range | | T _J , T _{stg} | - 55 to 150 | °C | |
| Soldering Recommendations (Peak Temperature) ^{d, e} | | | 260 | U | |

| THERMAL RESISTANCE RATINGS | | | | | | |
|---|--------------|-------------------|---------|---------|------|--|
| Parameter | | Symbol | Typical | Maximum | | |
| Maximum Junction-to-Ambient ^{b, f} | t ≤ 5 s | R _{thJA} | 52 | 65 | °C/W | |
| Maximum Junction-to-Case (Drain) | Steady State | R _{thJC} | 12.5 | 16 | | |

Notes:

a. Package limited

b. Surface Mounted on 1" x 1" FR4 board.

t = 5 s. C.

d. See Solder Profile (www.vishav.com/ppg?73257). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components. e.

Maximum under Steady State conditions is 110 °C/W f.

COMPLIANT

HALOGEN FREE



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| Parameter | Symbol | Test Conditions | Min. | Тур. | Max. | Unit | |
|---|-------------------------|--|------|-------|-------|-------|--|
| Static | | | | | | | |
| Drain-Source Breakdown Voltage | V _{DS} | $V_{GS} = 0 \text{ V}, \text{ I}_{D} = 250 \mu\text{A}$ | 20 | | | V | |
| V _{DS} Temperature Coefficient | $\Delta V_{DS}/T_{J}$ | L = 250 uA | | 23 | | mV/°C | |
| V _{GS(th)} Temperature Coefficient | $\Delta V_{GS(th)}/T_J$ | l _D = 250 μA | | - 3.3 | | | |
| Gate-Source Threshold Voltage | V _{GS(th)} | $V_{DS} = V_{GS}$, $I_D = 250 \ \mu A$ | 0.6 | | 1.4 | V | |
| Gate-Source Leakage | I _{GSS} | $V_{DS} = 0 V, V_{GS} = \pm 12 V$ | | | ± 8 | | |
| Zero Gate Voltage Drain Current | I _{DSS} | $V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}$ | | | - 1 | μA | |
| | | $V_{DS} = 20 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{J} = 55 ^{\circ}\text{C}$ | | | - 10 | 1 | |
| On-State Drain Current ^a | I _{D(on)} | $V_{DS} \le 5 \text{ V}, \text{ V}_{GS} = 4.5 \text{ V}$ | 10 | | | Α | |
| | _ | $V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 3.9 \text{ A}$ | | 0.037 | 0.046 | - Ω | |
| Drain-Source On-State Resistance ^a | R _{DS(on)} | $V_{GS} = 2.5 \text{ V}, \text{ I}_{D} = 3.3 \text{ A}$ | | 0.051 | 0.063 | | |
| Forward Transconductance ^a | 9 _{fs} | V _{DS} = 10 V, I _D = 3.9 A | | 14 | | S | |
| Dynamic ^b | | • | | | | | |
| Input Capacitance | C _{iss} | | | 350 | | pF | |
| Output Capacitance | C _{oss} | V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz | | 63 | | | |
| Reverse Transfer Capacitance | C _{rss} | | | 37 | | | |
| Total Gate Charge | | $V_{DS} = 10 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 5.1 \text{ A}$ | | 7.5 | 12 | nC | |
| | Qg | | | 3.5 | 5.5 | | |
| Gate-Source Charge | Q _{gs} | $V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V}, I_D = 5.1 \text{ A}$ | | 0.95 | | | |
| Gate-Drain Charge | Q _{gd} | | | 0.75 | | | |
| Gate Resistance | Rg | f = 1 MHz | | 3.5 | | Ω | |
| Turn-on Delay Time | t _{d(on)} | | | 10 | 15 | | |
| Rise Time | t _r | V _{DD} = 10 V, R _I = 2.4 Ω | | 12 | 20 | - ns | |
| Turn-Off Delay Time | t _{d(off)} | $V_{DD} = 10$ V, $H_{L} = 2.4$ S2 $I_{D} \cong 4.1$ A, $V_{GEN} = 4.5$ V, $R_{g} = 1 \Omega$ | | 18 | 30 | | |
| Fall Time | t _f | | | 12 | 20 | | |
| Turn-on Delay Time | t _{d(on)} | | | 5 | 10 | | |
| Rise Time | t _r | V _{DD} = 10 V, R _I = 2.4 Ω | | 12 | 20 | | |
| Turn-Off Delay Time | t _{d(off)} | $V_{DD} = 10 \text{ V}, \text{ H}_{L} = 2.4 \Omega^{2}$ $I_{D} \simeq 4.1 \text{ A}, \text{ V}_{\text{GEN}} = 10 \text{ V}, \text{ H}_{a} = 1 \Omega$ | | 15 | 25 | | |
| Fall Time | t _f | | | 10 | 15 | | |
| Drain-Source Body Diode Characteristic | cs | • | | | | | |
| Continuous Source-Drain Diode Current | ۱ _S | T _C = 25 °C | | | 4.5 | Δ | |
| Pulse Diode Forward Current | I _{SM} | | | | 15 | A | |
| Body Diode Voltage | V _{SD} | $I_{S} = 4.1 \text{ A}, V_{GS} = 0 \text{ V}$ | | 0.8 | 1.2 | V | |
| Body Diode Reverse Recovery Time | t _{rr} | | | 15 | 30 | ns | |
| Body Diode Reverse Recovery Charge | Q _{rr} | I _F = 4.1 A, dl/dt = 100 A/μs, T _J = 25 °C | | 8 | 20 | nC | |
| Reverse Recovery Fall Time | t _a | $F = 4.1 \text{ A}, \text{ u/ul} = 100 \text{ A/}\mu\text{s}, T_J = 25 \text{ C}$ | | 8 | | ns | |
| Reverse Recovery Rise Time | t _b | 1 | | 7 | | | |

Notes:

a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %

b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.





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T_C = - 55 °C

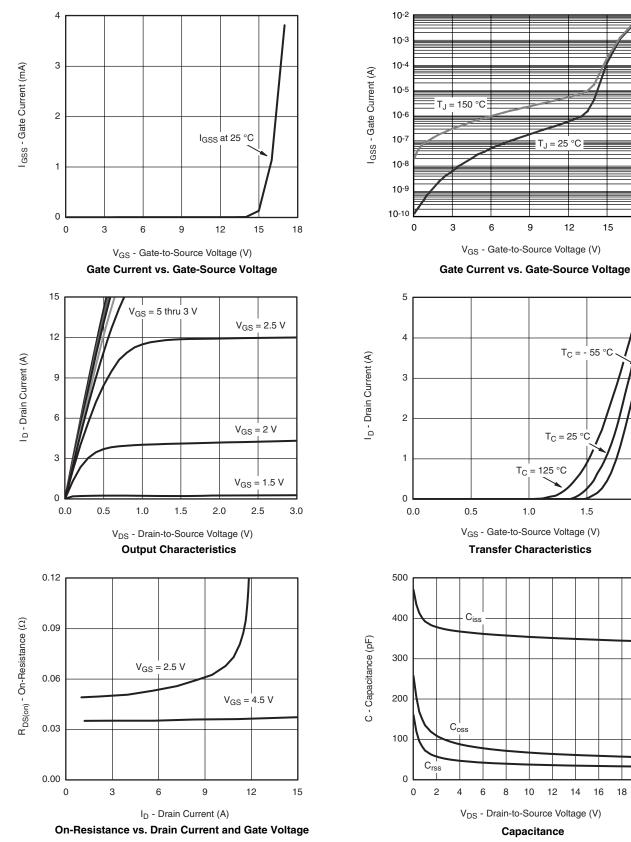
1.5

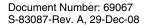
15

18

2.0

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



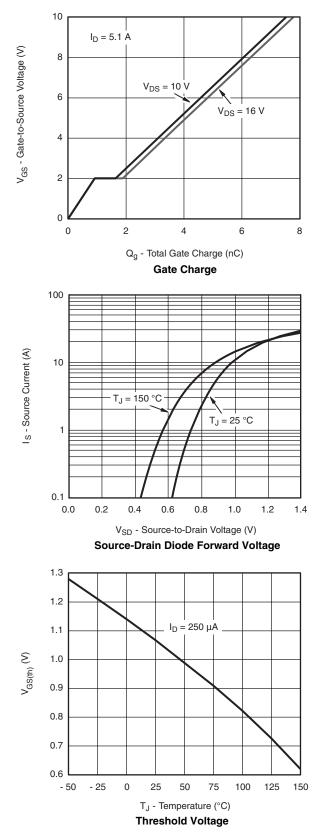


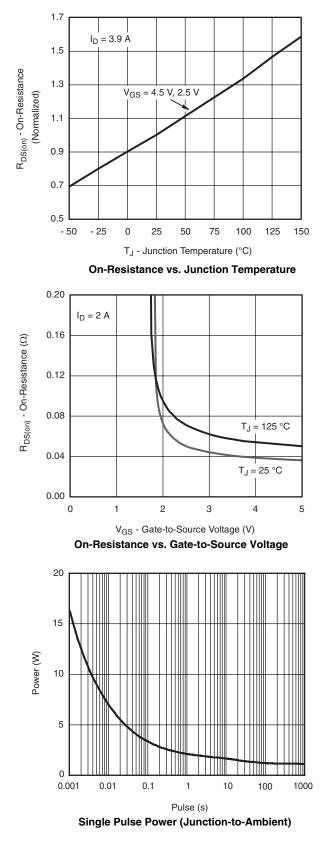
14 16 18 20

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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



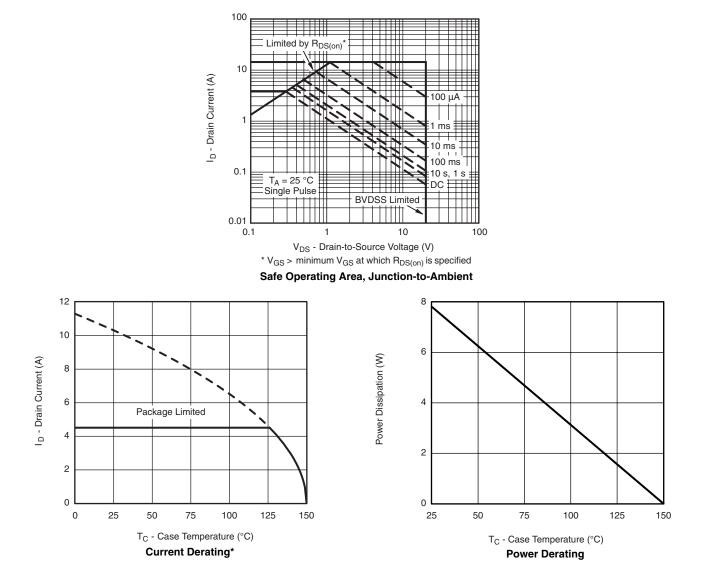


New Product



SiA906EDJ Vishay Siliconix

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

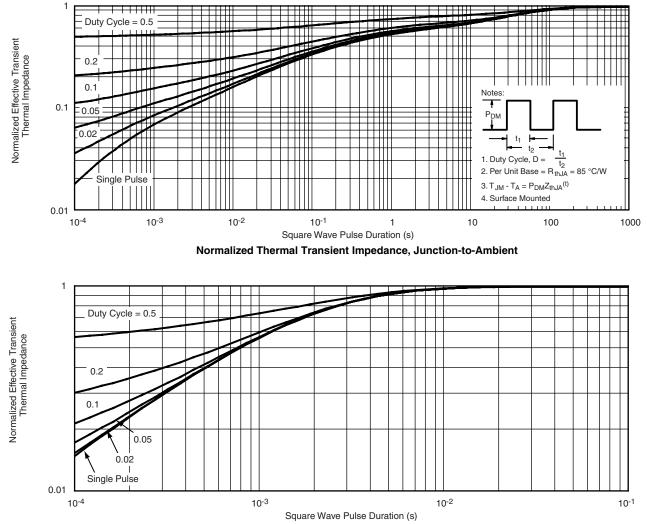


* The power dissipation P_D is based on $T_{J(max)}$ = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Foot

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <u>www.vishay.com/ppg?69067</u>.



PowerPAK[®] SC70-6L

VISHA

b PIN2 PIN1 PIN3 _ ₹



b

PIN3

__ ₿

PIN2

PIN1

¥

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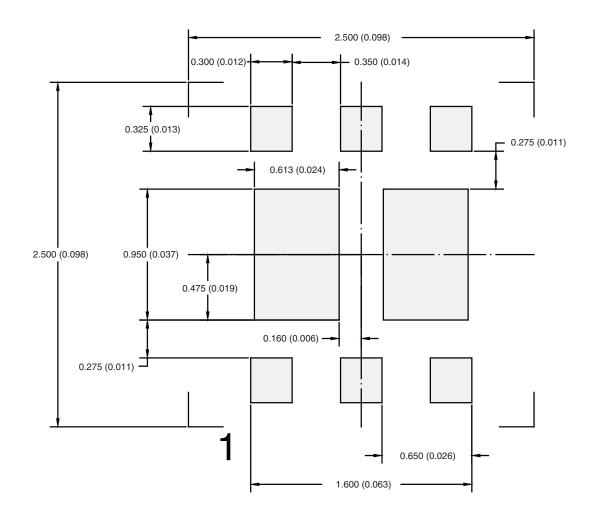
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Application Note 826

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RECOMMENDED PAD LAYOUT FOR PowerPAK® SC70-6L Dual



Dimensions in mm (inches)

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